

Yongqing Li

List of Publications by Year in descending order

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64
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218677

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citing authors

#	ARTICLE	IF	CITATIONS
1	Probing the magnetic polaron state in the ferromagnetic semiconductor HgCr_2Te_4 with muon-spin spectroscopy and resistance-fluctuation measurements. <i>Physical Review B</i> , 2022, 105, .		
2	Resistance anomaly and linear magnetoresistance in thin flakes of itinerant ferromagnet Fe_3GeTe_2 . <i>Chinese Physics Letters</i> , 2022, 39, 077501.	3.3	9
3	Magnetic Proximity Effect in an Antiferromagnetic Insulator/Topological Insulator Heterostructure with Sharp Interface. <i>Chinese Physics Letters</i> , 2021, 38, 057303.	3.3	2
4	On the anomalous low-resistance state and exceptional Hall component in hard-magnetic Weyl nanoflakes. <i>Science China: Physics, Mechanics and Astronomy</i> , 2021, 64, 1.	5.1	11
5	Influence of Device Geometry on Transport Properties of Topological Insulator Microflakes. <i>Chinese Physics Letters</i> , 2021, 38, 117302.	3.3	0
6	Epitaxial Growth and Transport Properties of Magnetic Weyl Semimetal $\text{Co}_3\text{Sn}_2\text{S}_2$ Thin Films. <i>ACS Applied Electronic Materials</i> , 2020, 2, 126-133.	4.3	22
7	Linear and Nonlinear Two-Terminal Spin-Valve Effect from Chirality-Induced Spin Selectivity. <i>ACS Nano</i> , 2020, 14, 15983-15991.	14.6	47
8	Giant enhancement of the in-plane critical field for thin Al films via proximity coupling to a topological insulator. <i>Physical Review B</i> , 2020, 102, .	3.2	0
9	Anomalous Hall Effect in Layered Ferrimagnet MnSb_2Te_4 *. <i>Chinese Physics Letters</i> , 2020, 37, 047301.	3.3	33
10	Robust Gapless Surface State against Surface Magnetic Impurities on $(\text{Bi}_0.5\text{Sb}_0.5)_2\text{Te}_3$ Evidenced by In-Situ Magnetotransport Measurements. <i>Physical Review Letters</i> , 2020, 124, 126601.	7.8	7
11	Transport in two-dimensional topological materials: recent developments in experiment and theory. <i>2D Materials</i> , 2020, 7, 022007.	4.4	92
12	Anomalous Hall effect in a magnetically extended topological insulator heterostructure. <i>Physical Review Materials</i> , 2020, 4, .	2.4	1
13	Magnetic-Competition-Induced Colossal Magnetoresistance in $\text{n-HgCr}_2\text{Te}_4$ -Type HgCr_2Te_4 under High Pressure. <i>Physical Review Letters</i> , 2019, 123, 047201.	7.8	9
14	Mn-doped topological insulators: a review. <i>Journal of Semiconductors</i> , 2019, 40, 081507.	3.7	22
15	Magnetic and transport properties of $\text{Zr}_2\text{NbCo}_2\text{Sn}$. <i>Journal of Physics Condensed Matter</i> , 2019, 31, 275702.	1.8	2
16	Unconventional Temperature Dependence of the Anomalous Hall Effect in HgCr_2Te_4 . <i>Physical Review Letters</i> , 2019, 123, 096601.	7.8	18
17	Quantized Conductance in Topological Insulators Revealed by the Shockley-Ramo Theorem. <i>Physical Review Letters</i> , 2019, 122, 146804.	7.8	7
18	Asperomagnetic order in diluted magnetic semiconductor $(\text{Ba},\text{Na})(\text{Zn},\text{Mn})_2\text{As}_2$. <i>Applied Physics Letters</i> , 2018, 112, .	3.3	13

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19	Proximity-induced magnetism and an anomalous Hall effect in Bi ₂ Se ₃ /LaCoO ₃ : a topological insulator/ferromagnetic insulator thin film heterostructure. <i>Nanoscale</i> , 2018, 10, 10041-10049.	5.6	30
20	Two-component anomalous Hall effect in a magnetically doped topological insulator. <i>Nature Communications</i> , 2018, 9, 1282.	12.8	40
21	All-Solid-State Synaptic Transistor with Ultralow Conductance for Neuromorphic Computing. <i>Advanced Functional Materials</i> , 2018, 28, 1804170.	14.9	335
22	Growth and transport properties of topological insulator Bi ₂ Se ₃ thin film on a ferromagnetic insulating substrate. <i>Chinese Physics B</i> , 2018, 27, 076801.	1.4	7
23	A Synaptic Transistor based on Quasi-2D Molybdenum Oxide. <i>Advanced Materials</i> , 2017, 29, 1700906.	21.0	304
24	Anomalous quantization trajectory and parity anomaly in Co cluster decorated BiSbTeSe ₂ nanodevices. <i>Nature Communications</i> , 2017, 8, 977.	12.8	34
25	Large negative magnetoresistance of a nearly Dirac material: Layered antimonide EuMnSb_2 . <i>Physical Review B</i> , 2017, 96, .	3.2	50
26	Electron-Nuclear Spin Interactions in the Quantum Hall Regime. <i>Springer Series in Solid-state Sciences</i> , 2017, , 431-475.	0.3	0
27	Single Crystal Growth and Spin Polarization Measurements of Diluted Magnetic Semiconductor (BaK)(ZnMn) ₂ As ₂ . <i>Scientific Reports</i> , 2017, 7, 14473.	3.3	25
28	Enhanced electron dephasing in three-dimensional topological insulators. <i>Nature Communications</i> , 2017, 8, 16071.	12.8	41
29	Effect of Different Substituted Groups on Excited-State Intramolecular Proton Transfer of 1-(Acylamino)-anthraquinone. <i>Journal of Physical Chemistry C</i> , 2017, 121, 14779-14786.	3.1	72
30	Thickness Dependence of the Quantum Anomalous Hall Effect in Magnetic Topological Insulator Films. <i>Advanced Materials</i> , 2016, 28, 6386-6390.	21.0	63
31	Giant semiclassical magnetoresistance in high mobility TaAs ₂ semimetal. <i>Applied Physics Letters</i> , 2016, 108, 042105.	3.3	67
32	Electron localization in ultrathin films of three-dimensional topological insulators. <i>Chinese Physics B</i> , 2016, 25, 117201.	1.4	2
33	Spin correlations and colossal magnetoresistance in HgCr_2Br_2 . <i>Physical Review B</i> , 2016, 94, .	3.2	15
34	High-pressure synthesis and characterization of the effective pseudospin $S=1/2$ XY pyrochlores $\text{R}_2\text{Pt}_2\text{O}_7$ (R=Er, Yb). <i>Physical Review B</i> , 2016, 93, .	3.2	20
35	Evidence for Half-Metallicity in HgCr_2Br_2 . <i>Physical Review Letters</i> , 2015, 115, 087002.	7.8	62
36	The physical mechanism of magnetic field controlled magnetocaloric effect and magnetoresistance in bulk PrGa compound. <i>Scientific Reports</i> , 2015, 5, 14970.	3.3	16

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37	Chemical potential fluctuations in topological insulator ($\text{Bi}_{0.5}\text{Sb}_{0.5}$) Te_3 -films visualized by photocurrent spectroscopy. 2D Materials, 2015, 2, 024012.	4.4	16
38	Homoepitaxial $\text{SrTiO}_3(111)$ Film with High Dielectric Performance and Atomically Well-Defined Surface. Scientific Reports, 2015, 5, 10634.	3.3	14
39	Observation of Anderson Localization in Ultrathin Films of Three-Dimensional Topological Insulators. Physical Review Letters, 2015, 114, 216601.	7.8	82
40	Proximity effect between a topological insulator and a magnetic insulator with large perpendicular anisotropy. Applied Physics Letters, 2014, 105, 092411.	3.3	37
41	Insight into vibration mode-resolved plasmon enhanced Raman optical activity. Journal of Colloid and Interface Science, 2014, 415, 165-168.	9.4	2
42	Parallel field magnetoresistance in topological insulator thin films. Physical Review B, 2013, 88, .	3.2	63
43	Current-induced nuclear spin depolarization at Landau level filling factor $\frac{1}{2}$. Physical Review B, 2012, 86, .	3.2	12
44	Highly tunable electron transport in epitaxial topological insulator ($\text{Bi}_1\text{Sb}_x\text{Te}_3$) thin films. Applied Physics Letters, 2012, 101, .	3.3	76
45	Transport properties of topological insulator Bi_2Se_3 thin films in tilted magnetic fields. Physica E: Low-Dimensional Systems and Nanostructures, 2012, 46, 236-240.	2.7	7
46	Local photocurrent generation in thin films of the topological insulator Bi_2Se_3 . Applied Physics Letters, 2012, 101, .	3.3	27
47	Electron transport properties of three-dimensional topological insulators. Frontiers of Physics, 2012, 7, 165-174.	5.0	26
48	Tunable surface conductivity in Bi_2Se_3 revealed in	3.2	226
49	Growth of Topological Insulator Bi_2Se_3 Thin Films on SrTiO_3 with Large Tunability in Chemical Potential. Advanced Functional Materials, 2011, 21, 2351-2355.	14.9	122
50	Aharonov-Casher Effect in Bi_2S_3 Interferometers. Physical Review Letters, 2011, 107, 016802.	7.8	573
51	Gate-Voltage Control of Chemical Potential and Weak Antilocalization in Bi_2S_3 . Physical Review Letters, 2010, 105, 176602.	7.8	573
52	Nature of the Spin Transition in the Half-filled Landau Level. Physical Review Letters, 2009, 102, 046803.	7.8	13
53	Single-electron switching in $\text{Al}_x\text{Ga}_{1-x}\text{As}$ Hall devices. Physical Review B, 2006, 74, .	3.2	20
54	Cavity enhanced Faraday rotation of semiconductor quantum dots. Applied Physics Letters, 2006, 88, 193126.	3.3	42

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55	Low-frequency noise in submicron GaAs/Al _x Ga _{1-x} As Hall devices. Journal of Magnetism and Magnetic Materials, 2005, 290-291, 1161-1164.	2.3	1
56	Magnetization reversal in elongated Fe nanoparticles. Physical Review B, 2005, 71, .	3.2	17
57	Modulation of Noise in Submicron GaAs/AlGaAs Hall Devices by Gating. Physical Review Letters, 2004, 93, 246602.	7.8	36
58	Magnetization reversal of iron nanoparticles studied by submicron Hall magnetometry. Journal of Applied Physics, 2003, 93, 7912-7914.	2.5	7
59	Hall magnetometry on a single iron nanoparticle. Applied Physics Letters, 2002, 80, 4644-4646.	3.3	65
60	Formation of a palladium carbide with a palladium-silicide-like structure in fullerene-C60/Pd multilayers. Materials Research Bulletin, 2000, 35, 551-557.	5.2	10
61	Investigation of High Pressure Induced Orientational Phase Transition in C60 Single Crystal. Physica Status Solidi (B): Basic Research, 1998, 207, 243-248.	1.5	1
62	Growth of C60 single crystal films on metal substrates. Thin Solid Films, 1998, 320, 179-183.	1.8	7
63	Metal-induced reconstruction of fullerene thin films: from dendritic to fractal growth. Journal of Physics Condensed Matter, 1998, 10, 9609-9621.	1.8	5
64	Study of Microstructure and Interfacial Interaction in Al-C60 Co-Evaporated Films. Physica Status Solidi A, 1997, 163, 403-409.	1.7	12